

74AHC2G00; 74AHCT2G00

Dual 2-input NAND gate

Rev. 02 — 12 January 2009

Product data sheet

1. General description

The 74AHC2G00; 74AHCT2G00 is a high-speed Si-gate CMOS device.

The 74AHC2G00; 74AHCT2G00 provides two 2-input NAND gates.

2. Features

- Symmetrical output impedance
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AHC2G00DP 74AHCT2G00DP	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74AHC2G00DC 74AHCT2G00DC	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AHC2G00GD 74AHCT2G00GD	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5\text{ mm}$	SOT996-2

4. Marking

Table 2. Marking

Type number	Marking code
74AHC2G00DP	A00
74AHCT2G00DP	C00
74AHC2G00DC	A00
74AHCT2G00DC	C00
74AHC2G00GD	A00
74AHCT2G00GD	C00

5. Functional diagram

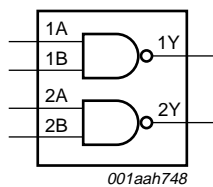


Fig 1. Logic symbol

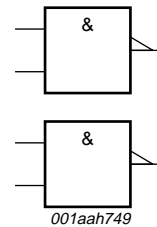


Fig 2. IEC logic symbol

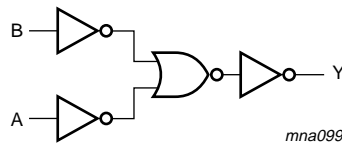
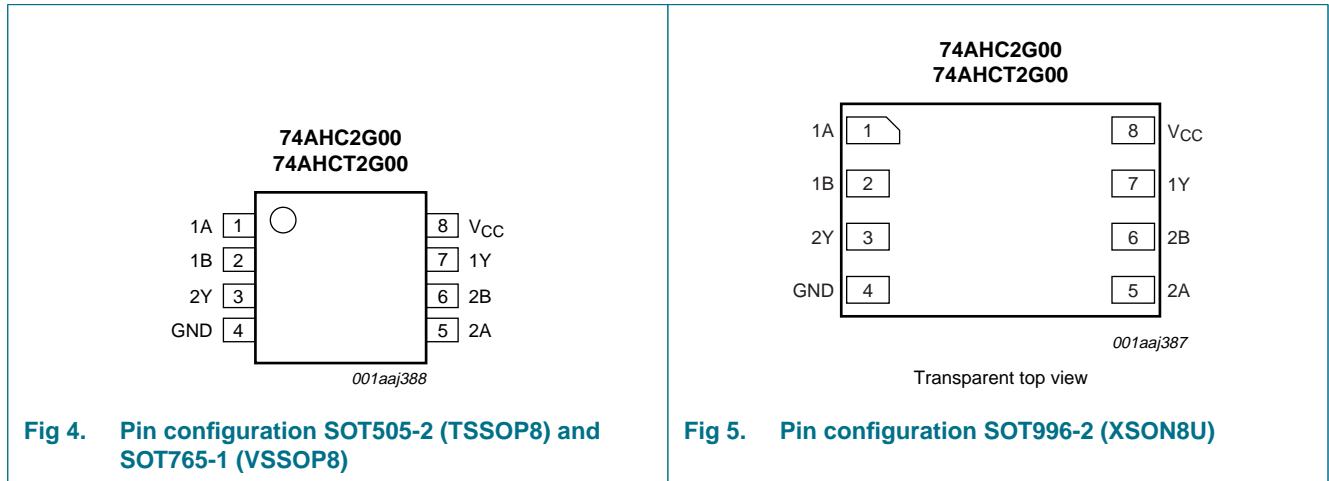


Fig 3. Logic diagram (one gate)

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input		Output
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	input voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	[1] -20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1] -	±20	mA
I_O	output current	-0.5 V < V_O < $V_{CC} + 0.5$ V	-	±25	mA
I_{CC}	supply current		-	75	mA
I_{GND}	ground current		-75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
 For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.
 For XSON8U package: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC2G00			74AHCT2G00			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.3$ V ± 0.3 V	-	-	100	-	-	-	ns/V
		$V_{CC} = 5.0$ V ± 0.5 V	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC2G00										
V_{IH}	HIGH-level input voltage	$V_{CC} = 2.0$ V	1.5	-	-	1.5	-	1.5	-	V
		$V_{CC} = 3.0$ V	2.1	-	-	2.1	-	2.1	-	V
		$V_{CC} = 5.5$ V	3.85	-	-	3.85	-	3.85	-	V

Table 7. Static characteristics ...continued
 Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -50 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -50 μA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = -50 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I _O = -8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 50 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	10	-	10	-	40	μA
C _I	input capacitance		-	1.5	10	-	10	-	10	pF
74AHCT2G00										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	-	10	-	40	μA
ΔI _{CC}	additional supply current	per input pin; V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C _I	input capacitance		-	1.5	10	-	10	-	10	pF

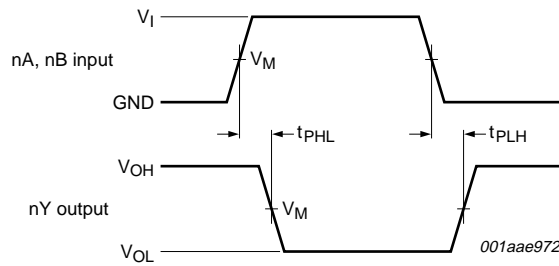
11. Dynamic characteristics

Table 8. Dynamic characteristics
GND = 0 V; for test circuit see Figure 7.

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC2G00										
t _{pd}	propagation delay	nA, nB to nY; see Figure 6 [1]								
		V _{CC} = 3.0 V to 3.6 V [2]								
		C _L = 15 pF	-	4.5	7.9	1.0	9.5	1.0	10.5	ns
		C _L = 50 pF	-	6.5	11.4	1.0	13.0	1.0	14.5	ns
		V _{CC} = 4.5 V to 5.5 V [3]								
		C _L = 15 pF	-	3.5	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF	-	4.9	7.5	1.0	8.5	1.0	9.5	ns
C _{PD}	power dissipation capacitance	per buffer; C _L = 50 pF; f _i = 1 MHz; V _i = GND to V _{CC}	[4]	-	17	-	-	-	-	pF
74AHCT2G00										
t _{pd}	propagation delay	nA, nB to nY; see Figure 6 [1]								
		V _{CC} = 4.5 V to 5.5 V [3]								
		C _L = 15 pF	1.0	3.6	6.2	1.0	7.1	1.0	8.0	ns
		C _L = 50 pF	1.0	5.0	7.9	1.0	9.0	1.0	10.0	ns
C _{PD}	power dissipation capacitance	per buffer; C _L = 50 pF; f _i = 1 MHz; V _i = GND to V _{CC}	[4]	-	18	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [2] Typical values are measured at V_{CC} = 3.3 V.
- [3] Typical values are measured at V_{CC} = 5.0 V.
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

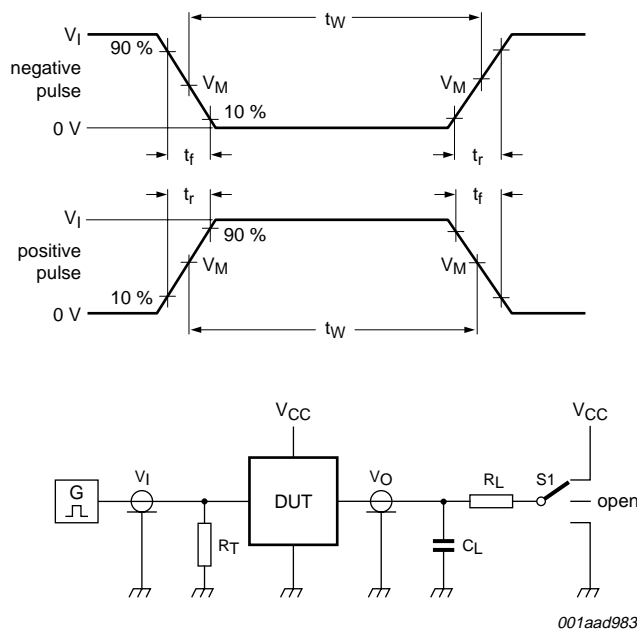


Measurement points are given in [Table 9](#).
 Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. The input (nA and nB) to output (nY) propagation delays.

Table 9. Measurement points

Type	Input V_M	Output V_M
74AHC2G00	$0.5V_{CC}$	$0.5V_{CC}$
74AHCT2G00	1.5 V	$0.5V_{CC}$



Test data is given in [Table 10](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 7. Test circuit for measuring switching times

Table 10. Test data

Type	Input		Load		S1 position
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}
74AHC2G00	V_{CC}	≤ 3 ns	15 pF, 50 pF	1 k Ω	open
74AHCT2G00	3 V	≤ 3 ns	15 pF, 50 pF	1 k Ω	open

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

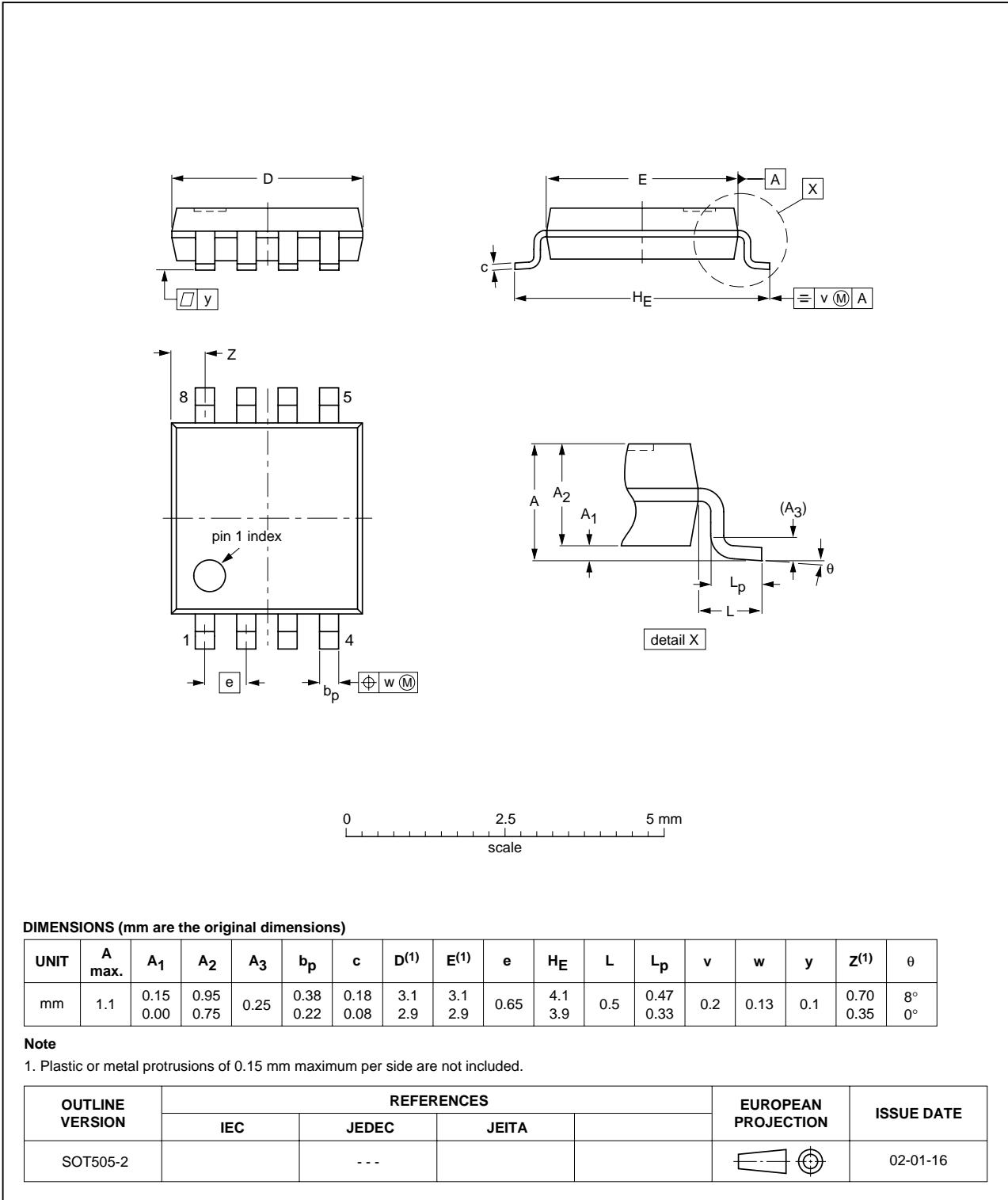


Fig 8. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

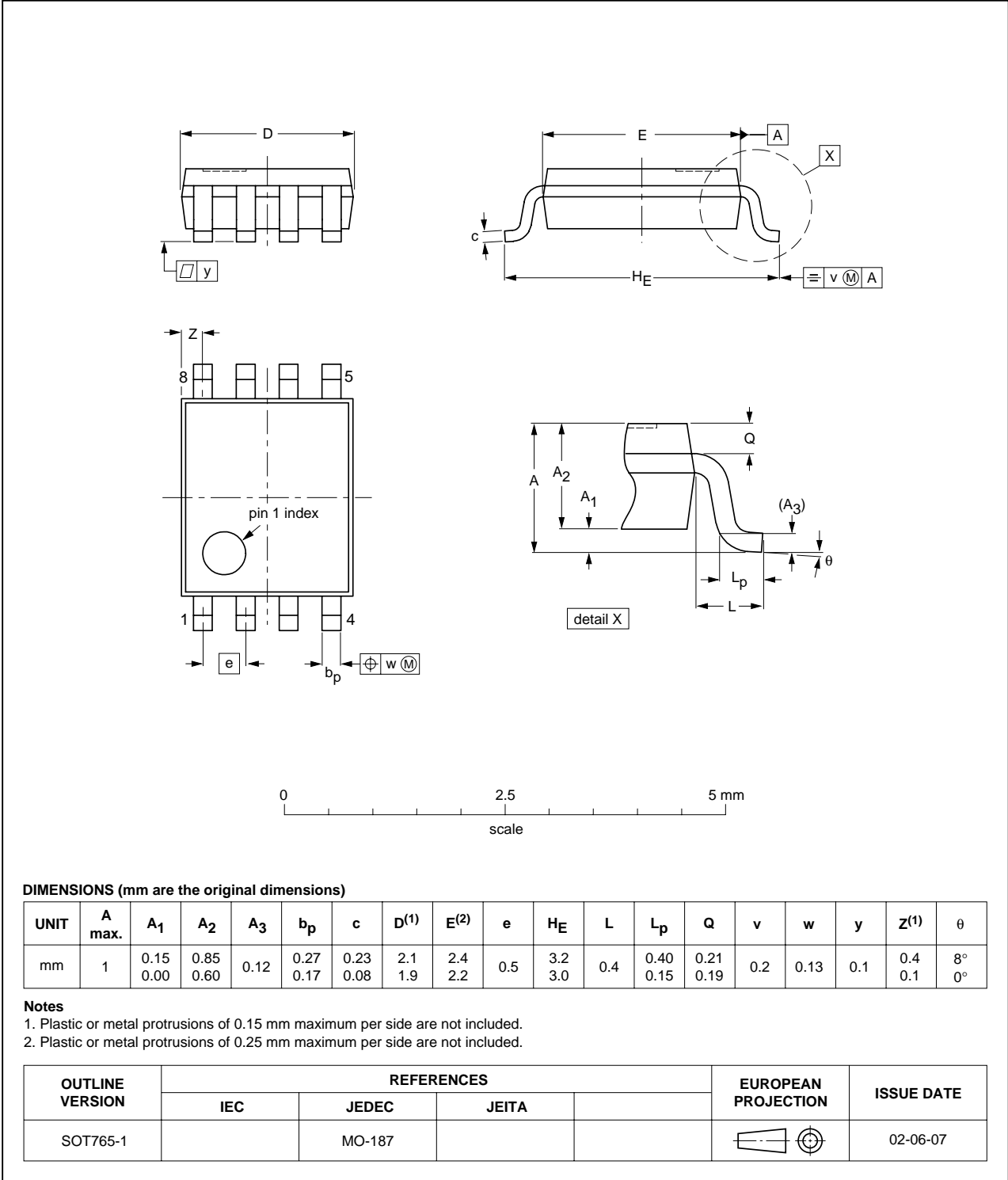


Fig 9. Package outline SOT765-1 (VSSOP8)

XSON8U: plastic extremely thin small outline package; no leads;
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

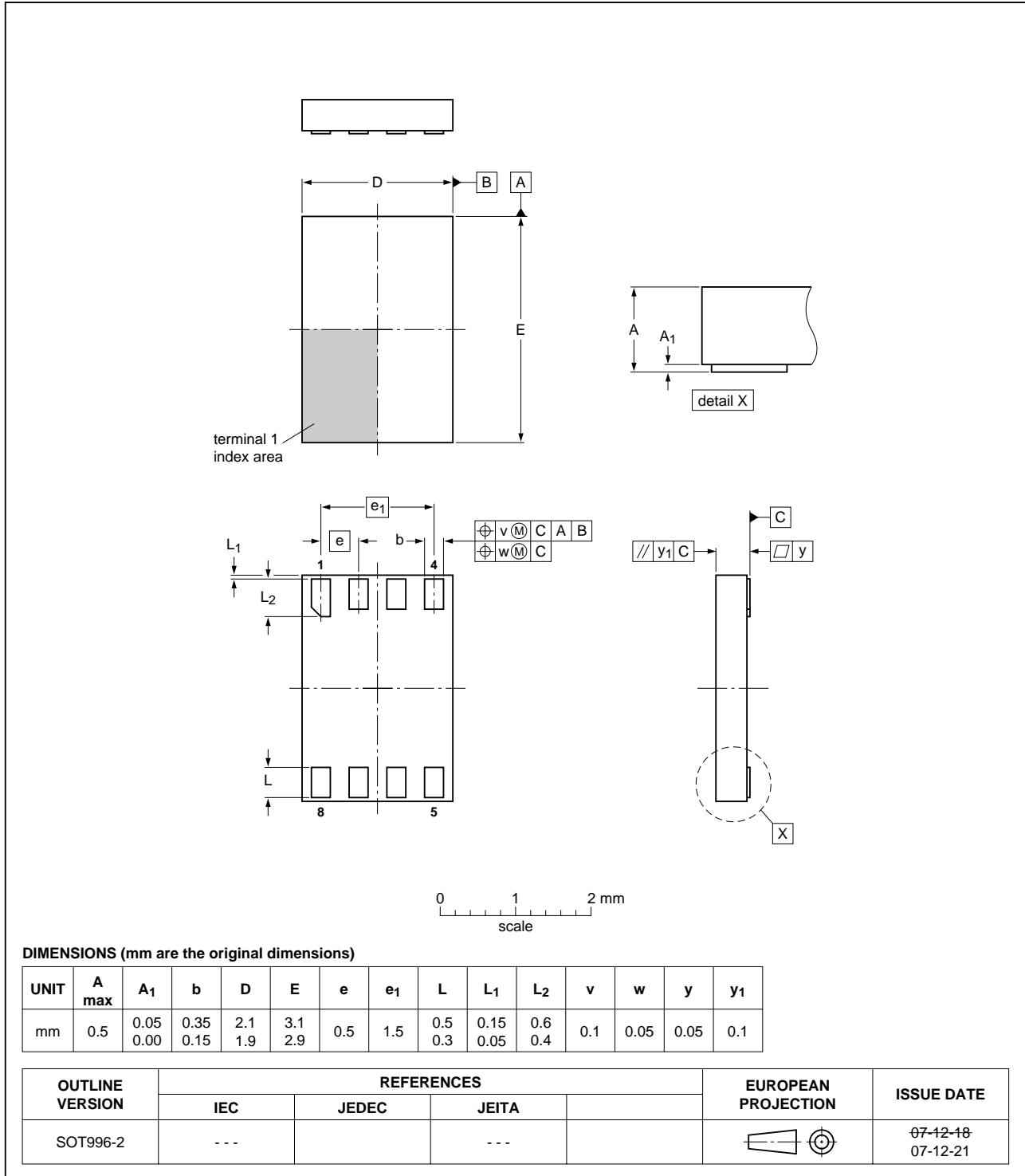


Fig 10. Package outline SOT996-2 (XSON8U)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G00_2	20090112	Product data sheet	-	74AHC_AHCT2G00_1
Modifications:		<ul style="list-style-type: none">The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.Legal texts have been adapted to the new company name where appropriate.Added type number 74AHC2G00GD and 74AHCT2G00GD (XSON8U package).		
74AHC_AHCT2G00_1	20040101	Product specification	-	-

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16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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